IN THE CLAIMS:

Please amend Claims 10, 11, 12, 14, 15 and 18 in "clean" format, as follows:

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10. (Amended) A semiconductor integrated circuit comprising:

a pad to which an input signal is externally input;

a source follower circuit including, a transistor having a gate connected to said pad and a source for producing an output signal;

wherein a parasitic capacitance is created between said pad and a semiconductor substrate, and said source of the source follower circuit is connected to the semiconductor substrate side of the parasitic capacitance so as to charge and discharge the parasitic capacitance by the output signal of said source follower circuit.

11. (Amended) The semiconductor integrated circuit defined in Claim 10, further comprising an island region on the upper surface of said semiconductor substrate containing impurities of a second conductivity type, and a pad formed on said island region via an oxide film; and wherein said semiconductor substrate contains impurities of a first conductivity type; and wherein an output terminal of said source follower circuit is connected to said island region.

12. (Amended) The semiconductor integrated circuit defined in Claim 11, wherein said island region is surrounded with an isolation region containing impurities of said first conductivity type.

14. (Amended) The semiconductor integrated circuit defined in Claim 11, wherein said output terminal is connected to said island region by way of a metal conductor.

15. (Amended) The semiconductor integrated circuit defined in Claim 10, wherein an input impedance of an input stage circuit is set to a first value, and the parasitic capacitance is set to as a second value, the first value being higher than the second value.

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18. (Amended) The semiconductor integrated circuit defined in Claim 17, wherein said field effect transistor has a drain connected to a power source, and a source connected to a ground via a constant current source, for producing said output signal.